IN THE CLAIMS

(Currently amended) A semiconductor device having a pad region and a 1. circuit region, comprising:

a low-k dielectric film on [a] the pad region and [a] the circuit region a substrate, the low-k dielectric film having a dielectric constant of no more than 3;

an insulating film on the low-k dielectric film of the pad region, the insulating film having higher strength than the low-k dielectric film;

multi-layer wirings on the insulating film of the pad region and on the low-k dielectric film of the circuit region; and

a bonding pad on an outermost wiring of the multi-layer wirings of the pad region.

- (Currently amended) The semiconductor device according to claim 1, wherein 2. sidewalls of the wirings in the pad region are surrounded by the insulating film.
- (Previously presented) The semiconductor device according to claim 1, wherein the low-k dielectric film is an insulating film containing silicon, carbon, oxygen, and hydrogen.
- (Currently amended) A semiconductor device having a pad region and a 4. circuit region, comprising:

multi-layer low-k dielectric films on [a]the pad region and [a]the circuit region of a substrate, each of the multi-layer low-k dielectric films having a dielectric constant of no more than 3;

insulating films on each of the multi-layer low-k dielectric films of the pad region, each of the insulating films having higher strength than each of the multi-layer low-k dielectric films;

wirings on each of the insulating films of the pad region and on each of the low-k dielectric films of the circuit region; and

- a bonding pad on an outermost wiring of the wirings of the pad region.
- (Previously presented) The semiconductor device according to claim 4, 5. wherein sidewalls of the wirings in the pad region are surrounded by the insulating films.

(cancelled) Claims 6-9

(Previously presented) The semiconductor device according to claim 1, 10. wherein the low-k dielectric film is a polymer film containing hydrogen and carbon.